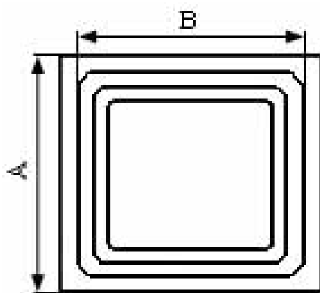
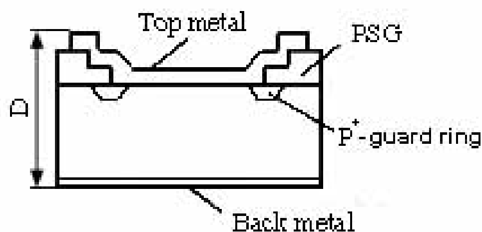
SCHOTTKY DIODES KDN-03020.

PRELIMINARY

Rev.1. Feb. 2010

VSP-MIKRON	3A/20V. Die Size-55mil.			
Electrical Characteristics	**Symbol**	**Unit**	**Spec. limit**	**Die Sort**
Breakdown Voltage @ I_R=10mA	V_{BR}	V	20	25
Average Rectified Forward Current	$I_{F(AV)}$	A	3,0	-
DC Forward Voltage @ 25˚C, I_F=3,0A	V_F	V	0,48	0,45
Maximum Reverse Current @ 25˚C, V_R=25V 25˚C, V_R=20V 125˚C, V_R=20V	I_R	mA	- 0,080 35,0	0,080 0,060 33,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	80	-
Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., T_J<150˚C.	I_{RRM}	A	2,0	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J	˚C	150	





DIM	ITEM	µm
A_X A_y	Wafer Form Die Size	1400 1400
B_X B_y	Top Metal Size	1260 1260
D	Thickness	300max.
Scribe line Width		80

Top metal: a) **Al** – for Wire Bonding;

b) ***Al-Ni-Ag***; - for Soldering

*Backside metal: **Ti-Ni-Ag**.*

www.vsp-mikron.com